## 2SC5896

## Silicon NPN epitaxial planar type

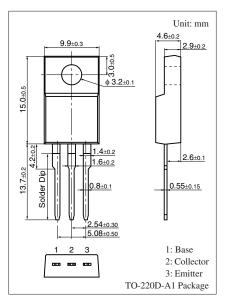
Power supply for Audio & Visual equipments such as TVs and VCRs Industrial equipments such as DC-DC converters

#### ■ Features

- ullet High-speed switching ( $t_{stg}$ : storage time/ $t_f$ : fall time is short)
- ullet Low collector-emitter saturation voltage  $V_{\text{CE(sat)}}$
- Superior forward current transfer ratio h<sub>FE</sub> linearity
- TO-220D built-in: Excellent package with withstand voltage 5 kV guaranteed

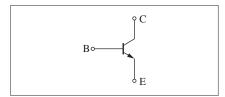
### ■ Absolute Maximum Ratings $T_C = 25$ °C

Parameter		Symbol	Rating	Unit	
Collector-base voltage (Emitter open)		$V_{CBO}$	60	V	
Collector-emitter voltage (Base open)		V <sub>CEO</sub>	60	V	
Emitter-base voltage (Collector open)		$V_{EBO}$	6	V	
Collector current		$I_C$	3	A	
Peak collector current		$I_{CP}$	5	A	
Collector power	$T_C = 25^{\circ}C$	$P_{C}$	15	W	
dissipation	$T_a = 25^{\circ}C$		2		
Junction temperature		T <sub>j</sub>	150	°C	
Storage temperature		T <sub>stg</sub>	-55 to +150	°C	



Marking Symbol: C5896

#### Internal Connection



### ■ Electrical Characteristics $T_C = 25$ °C $\pm 3$ °C

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	$I_C = 10 \text{ mA}, I_B = 0$	60			V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = 60 \text{ V}, I_{E} = 0$			100	μΑ
Collector-emitter cutoff current (Base open)	$I_{CEO}$	$V_{CE} = 60 \text{ V}, I_{B} = 0$			100	μΑ
Forward current transfer ratio	h <sub>FE1</sub>	$V_{CE} = 4 \text{ V}, I_{C} = 0.2 \text{ A}$	60			_
	h <sub>FE2</sub>	$V_{CE} = 4 \text{ V}, I_{C} = 1 \text{ A}$	80		250	_
	h <sub>FE3</sub>	$V_{CE} = 4 \text{ V}, I_{C} = 3 \text{ A}$	30			_
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_C = 3 \text{ A}, I_B = 0.375 \text{ A}$			0.6	V
Transition frequency	$f_T$	$V_{CE} = 10 \text{ V}, I_{C} = 0.1 \text{ A}, f = 10 \text{ MHz}$		100		MHz
Turn-on time	t <sub>on</sub>	I <sub>C</sub> = 1 A, Resistance loaded		0.2		μs
Storage time	t <sub>stg</sub>	$I_{B1} = 0.1 \text{ A}, I_{B2} = -0.1 \text{ A}$		0.75		μs
Fall time	$t_{\mathrm{f}}$	$V_{CC} = 50 \text{ V}$		0.15		μs

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

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